

BIPOLAR ANALOG INTEGRATED CIRCUIT $\mu PC3221GV$

5 V AGC AMPLIFIER + VIDEO AMPLIFIER

DESCRIPTION

The μ PC3221GV is a silicon monolithic IC designed for use as AGC amplifier for digital CATV, cable modem systems. This IC consists of gain control amplifier and video amplifier.

The package is 8-pin SSOP suitable for surface mount.

This IC is manufactured using our 10 GHz fr NESAT II AL silicon bipolar process. This process uses silicon nitride passivation film. This material can protect chip surface from external pollution and prevent corrosion/migration. Thus, this IC has excellent performance, uniformity and reliability.

FEATURES

- Low distortion : $IM_3 = 56 dBc TYP$. @ single-ended output, $V_{out} = 0.7 V_{p-p}/tone$
- Low noise figure : NF = 4.2 dB TYP.
- Wide AGC dynamic range
 - : GCR = 50 dB TYP. @ input prescribe
- On-chip video amplifier
- r : Vout = 1.0 Vp-p TYP. @ single-ended output
- Supply voltage : Vcc = 5.0 V TYP.
- Packaged in 8-pin SSOP suitable for surface mounting

APPLICATION

• Digital CATV/Cable modem receivers

ORDERING INFORMATION

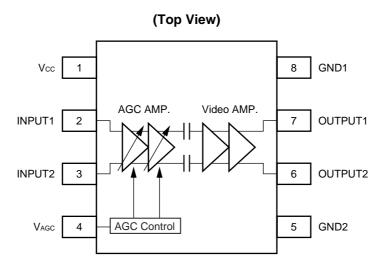
Part Number	Package	Supplying Form
<i>µ</i> РС3221GV-E1-А	8-pin plastic SSOP (4.45 mm (175))	 Embossed tape 8 mm wide Pin 1 indicates pull-out direction of tape Qty 1 kpcs/reel

Remark To order evaluation samples, contact your nearby sales office. Part number for sample order: μPC3221GV-A

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

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INTERNAL BLOCK DIAGRAM AND PIN CONNECTIONS



PRODUCT LINE-UP OF 5 V AGC AMPLIFIER

Part Number	lcc (mA)	Gмах (dB)	GміN (dB)	GCR (dB)	NF (dB)	IM ₃ (dBc) ^{Note}	Package
μPC3217GV	23	53	0	53	6.5	50	8-pin SSOP (4.45 mm (175))
μPC3218GV	23	63	10	53	3.5	50	
μPC3219GV	36.5	42.5	0	42.5	9.0	58	
μPC3221GV	33	60	10	50	4.2	56	

Note $f_1 = 44$ MHz, $f_2 = 45$ MHz, $V_{out} = 0.7$ V_{p-p} /tone, single-ended output

PIN EXPLANATIONS

Pin No.	Pin Name	Applied Voltage (V)	Pin Voltage (V) ^{Note}	Function and Application	Internal Equivalent Circuit
1	Vcc	4.5 to 5.5	_	Power supply pin. This pin should be externally equipped with bypass capacitor to minimize ground impedance.	
2	INPUT1		1.29	Signal input pins to AGC amplifier. This pin should be coupled with capacitor for DC cut.	AGC Control
3	INPUT2		1.29		
4	Vagc	0 to Vcc	_	Gain control pin. This pin's bias govern the AGC output level. Minimum Gain at V _{AGC} : 0 to 0.5 V Maximum Gain at V _{AGC} : 3 to 3.5 V Recommended to use AGC voltage with externally resister (example: 1 k Ω).	AGC Amp.
5	GND2	0	_	Ground pin. This pin should be connected to system ground with minimum inductance. Ground pattern on the board should be formed as wide as possible.	
6	OUTPUT2	_	2.28	Signal output pins of video amplifier. This pin should be coupled with capacitor for DC cut.	
7	OUTPUT1	-	2.28		
8	GND1	0	-	Ground pin. This pin should be connected to system ground with minimum inductance. Ground pattern on the board should be formed as wide as possible. All ground pins must be connected together with wide ground pattern to decrease impedance difference.	

Note Pin voltage is measured at Vcc = 5.0 V.

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Test Conditions	Ratings	Unit
Supply Voltage	Vcc	T _A = +25°C	6.0	V
Gain Control Voltage Range	VAGC	T _A = +25°C	0 to Vcc	V
Power Dissipation	Po	T _A = +85°C Note	250	mW
Operating Ambient Temperature	TA		-40 to +85	°C
Storage Temperature	Tstg		–55 to +150	°C

Note Mounted on double-sided copper-clad 50 \times 50 \times 1.6 mm epoxy glass PWB

RECOMMENDED OPERATING RANGE

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Supply Voltage	Vcc		4.5	5.0	5.5	V
Operating Ambient Temperature	TA	Vcc = 4.5 to 5.5 V	-40	+25	+85	°C
Gain Control Voltage Range	VAGC		0	-	3.5	V
Operating Frequency Range	fвw		10	45	100	MHz

ELECTRICAL CHARACTERISTICS

(TA = +25°C, Vcc = 5 V, f = 45 MHz, Zs = 50 Ω , ZL = 250 Ω , single-ended output)

Parameter	Symbol	Test Conditions		MIN.	TYP.	MAX.	Unit
DC Characteristics							
Circuit Current	lcc	No input signal	Note 1	26	33	41	mA
AGC Pin Current	IAGC	No input signal, VAGC = 3.5 V	Note 1	-	16	50	μA
AGC Voltage High Level	VAGC (H)	@ Maximum gain	Note 1	3.0	-	3.5	V
AGC Voltage Low Level	VAGC (L)	@ Minimum gain	Note 1	0	-	0.5	V
RF Characteristics							
Maximum Voltage Gain	Gmax	$V_{AGC} = 3.0 \text{ V}, \text{ P}_{in} = -60 \text{ dBm}$	Note 1	57	60	63	dB
Middle Voltage Gain 1	GMID1	$V_{AGC} = 2.2 \text{ V}, \text{ P}_{in} = -60 \text{ dBm}$	Note 1	47.5	50.5	53.5	dB
Middle Voltage Gain 2	GMID2	$V_{AGC} = 1.2 \text{ V}, \text{ P}_{in} = -30 \text{ dBm}$	Note 1	18	21	24	dB
Minimum Voltage Gain	Gmin	$V_{AGC} = 0.5 \text{ V}, \text{ Pin} = -30 \text{ dBm}$	Note 1	6	10	14	dB
Gain Control Range (input prescribe)	GCRin	V _{AGC} = 0.5 to 3.0 V	Note 1	43	50	-	dB
Gain Control Range (output prescribe)	GCRout	Vout = 1.0 Vp-p	Note 1	36	40	-	dB
Gain Slope	Gslope	Gain (@ V _{AGC} = 2.2 V) – Gain = 1.2 V)	(@ V _{AGC} Note 1	26.5	29.5	32.5	dB/V
Maximum Output Voltage	Voclip	V _{AGC} = 3.0 V (@ Maximum ga	in) Note 1	2.0	2.8	-	V _{p-p}
Noise Figure	NF	V _{AGC} = 3.0 V (@ Maximum ga	in) Note 3	_	4.2	5.7	dB
3rd Order Intermodulation Distortion 1	IM31	$ f_1 = 44 \text{ MHz}, f_2 = 45 \text{ MHz}, Z_L = \\ P_{in} = -30 \text{ dBm/tone}, \\ V_{out} = 0.7 \text{ V}_{P\text{-}P}/\text{tone} (@ \text{ single-e}) \\ output) $,	43	47	_	dBc
3rd Order Intermodulation Distortion 2	IM32	$ f_1 = 44 \text{ MHz}, f_2 = 45 \text{ MHz}, Z_L = \\ V_{AGC} = 3.0 \text{ V} (@ \text{ Maximum ga} \\ V_{out} = 0.7 \text{ V}_{P\text{-}P}/\text{tone} (@ \text{ single-e} \\ output) $	in),	50	56	_	dBc
Gain Difference of OUTPUT1 and OUTPUT2	⊿G	$V_{AGC} = 3.0 \text{ V}, \text{ Pin} = -60 \text{ dBm},$ $\Delta G = G (@ \text{ Pout1}) - G (@ \text{ Pout2})$	2) Note 1, 2	-0.5	0	+0.5	dB

Notes 1. By measurement circuit 1

- 2. By measurement circuit 2
- 3. By measurement circuit 3

STANDARD CHARACTERISTICS (TA = +25°C, Vcc = 5 V, Zs = 50 Ω)

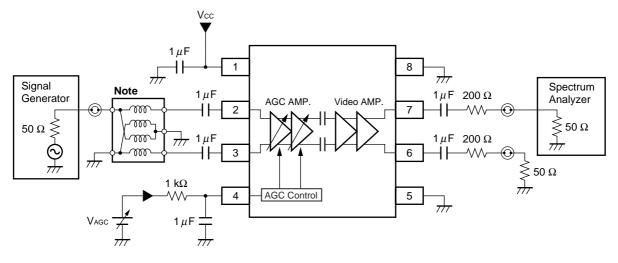
Parameter	Symbol	Test Conditions	Reference Value	Unit
Noise Figure 2	NF2	Gain reduction = -10 dBm Note 2	6.0	dB
Noise Figure 3	NF3	Gain reduction = -20 dBm Note 2	9.5	dB
Output Voltage	Vout	P _{in} = -56 to -16 dBm Note 1	1.0	V _{p-p}
Input Impedance	Zin	V _{AGC} = 0.5 V, f = 45 MHz Note 3	0.9 k – j1.4 k	Ω
Output Impedance	Zout	V _{AGC} = 0.5 V, f = 45 MHz Note 3	9.0 + j1.9	Ω
Input 3rd Order Distortion Intercept Point	IIΡ₃	$ \begin{array}{l} V_{AGC} = 0.5 \ V \ (@ \ Minimum \ gain), \\ f_1 = 44 \ MHz, \ f_2 = 45 \ MHz, \\ Z_L = 250 \ \Omega \ (@ \ single-ended \ output) \\ \hline \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \$	+2.5	dBm

Notes 1. By measurement circuit 1

2. By measurement circuit 3

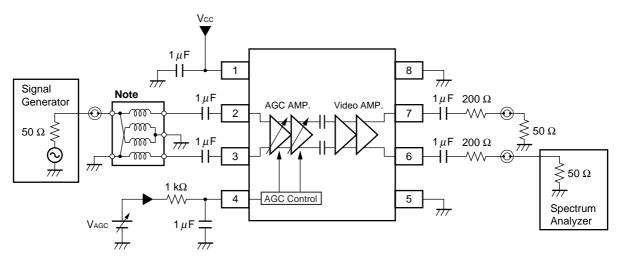
3. By measurement circuit 4

MEASUREMENT CIRCUIT 1



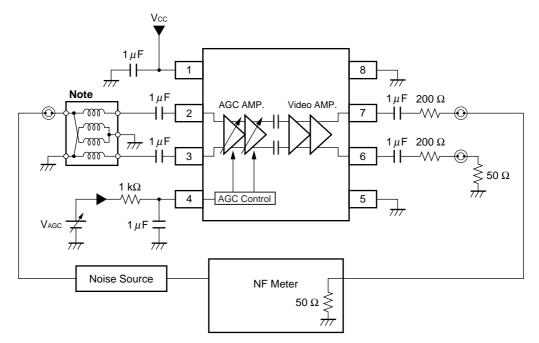
Note Balun Transformer: TOKO 617DB-1010 B4F (Double balanced type)

MEASUREMENT CIRCUIT 2



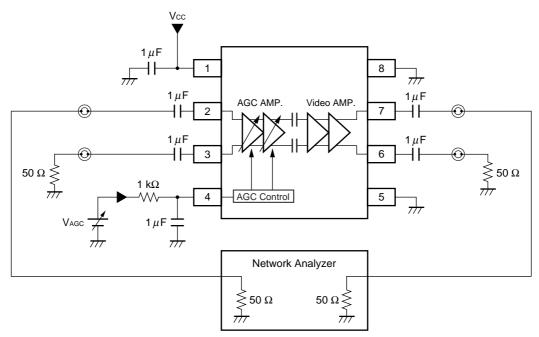
Note Balun Transformer: TOKO 617DB-1010 B4F (Double balanced type)

MEASUREMENT CIRCUIT 3



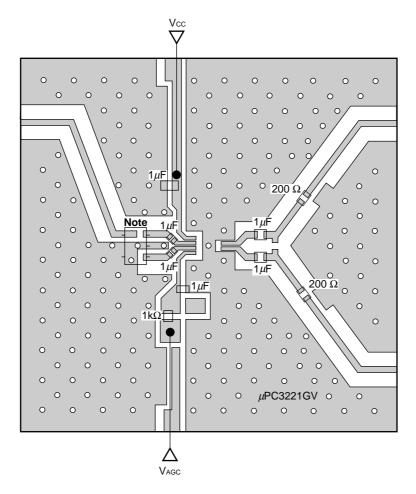
Note Balun Transformer: TOKO 617DB-1010 B4F (Double balanced type)





The application circuits and their parameters are for reference only and are not intended for use in actual design-ins.

★ ILLUSTRATION OF THE TEST CIRCUIT ASSEMBLED ON EVALUATION BOARD (MEASUREMENT CIRCUIT 1)



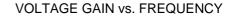
Note Balun Transformer

Remarks

- 1. Back side: GND pattern
- 2. Solder plated on pattern
- 3. o: Through hole

★ TYPICAL CHARACTERISTICS (T_A = +25°C , unless otherwise specified)

CIRCUIT CURRENT vs. SUPPLY VOLTAGE



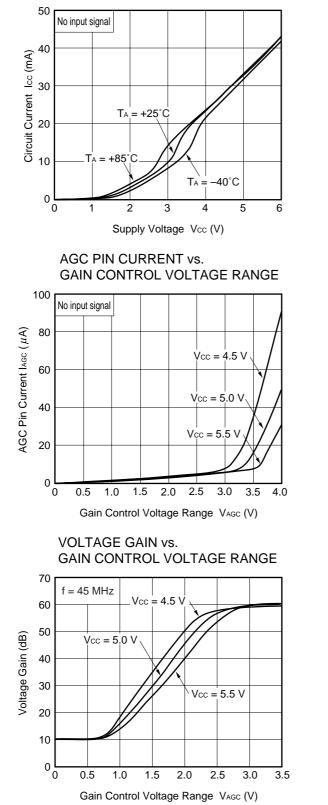
 $V_{AGC} = 3.0 V (P_{in} = -60 \text{ dBm})$

 $V_{AGC} = 1.6 V (P_{in} = -60 \text{ dBm})$

70

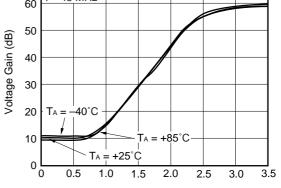
60 50

40



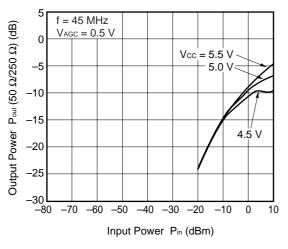


30 Voltage Gain (dB) 20 Vagc 0.5 V (Pin -30 dBm) 10 0 -10 -20 -30 -40 Vcc = 5.5 V 5.0 V 4.5 V -----50 -60 , 10 100 1 000 Frequency f (MHz) AGC PIN CURRENT vs. GAIN CONTROL VOLTAGE RANGE 100 No input signal AGC Pin Current lacc (μ A) 80 60 T_A = +85°C 40 $T_A = -40^{\circ}C$ 20 T_A = +25°C 0 0 0.5 1.0 1.5 2.0 2.5 3.0 3.5 4.0 Gain Control Voltage Range VAGC (V) VOLTAGE GAIN vs. GAIN CONTROL VOLTAGE RANGE 70 Vcc = 5.0 Vf = 45 MHz 60

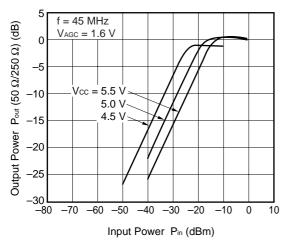


Gain Control Voltage Range VAGC (V)

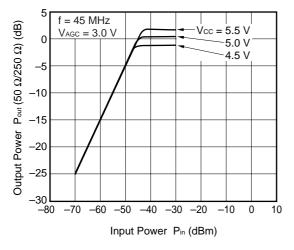
OUTPUT POWER vs. INPUT POWER



OUTPUT POWER vs. INPUT POWER

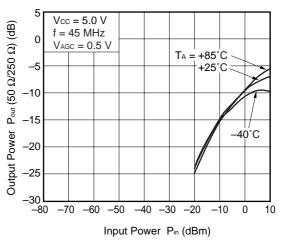


OUTPUT POWER vs. INPUT POWER

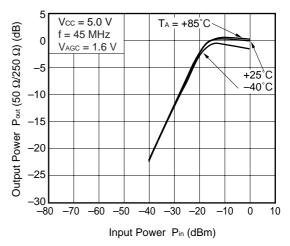


Remark The graphs indicate nominal characteristics.

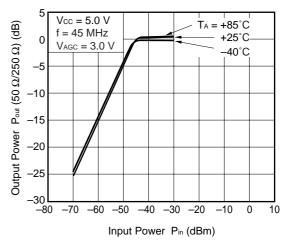
OUTPUT POWER vs. INPUT POWER

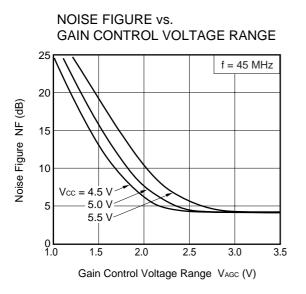


OUTPUT POWER vs. INPUT POWER

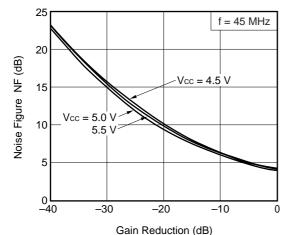


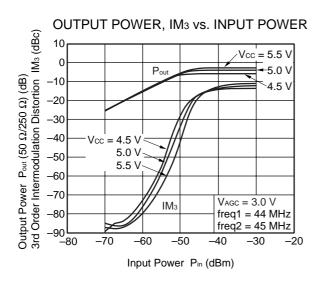
OUTPUT POWER vs. INPUT POWER





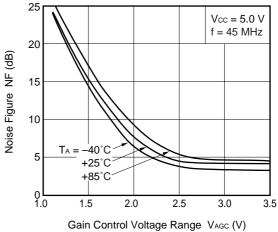
NOISE FIGURE vs. GAIN REDUCTION



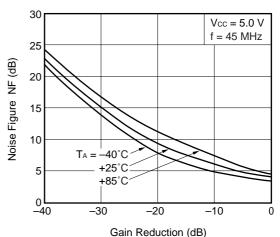


Remark The graphs indicate nominal characteristics.

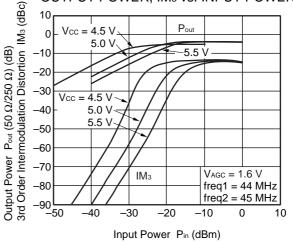
NOISE FIGURE vs. GAIN CONTROL VOLTAGE RANGE

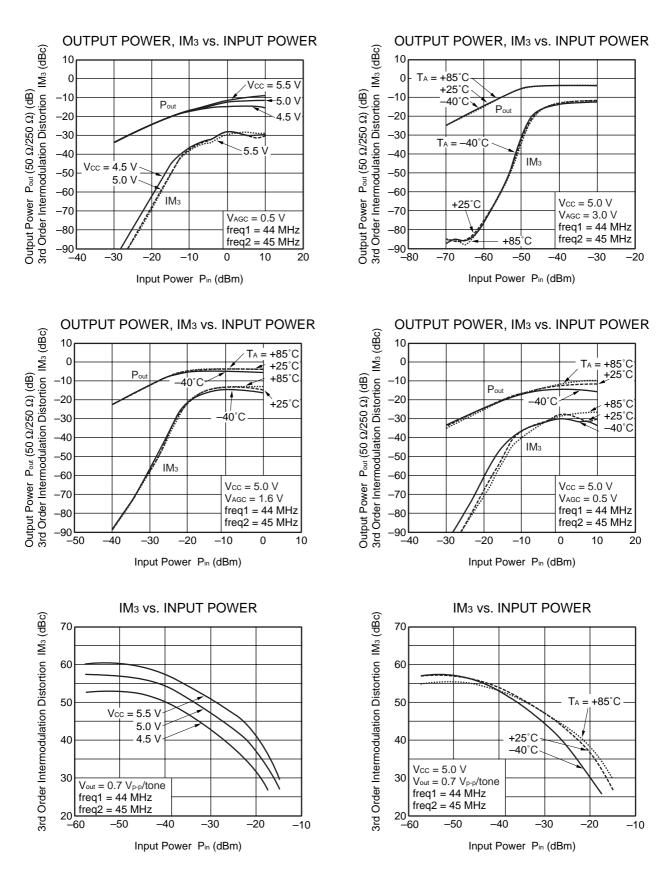


NOISE FIGURE vs. GAIN REDUCTION



OUTPUT POWER, IM3 vs. INPUT POWER

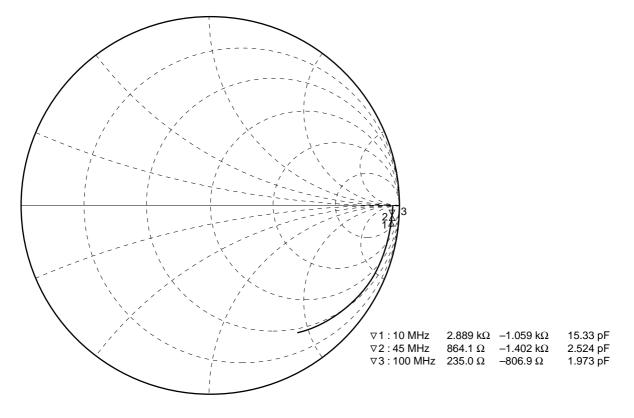




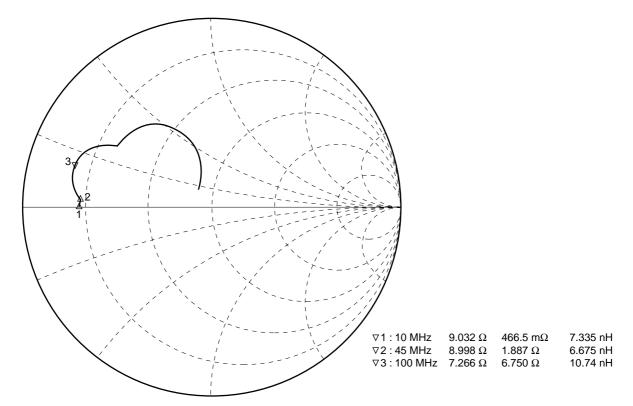
Remark The graphs indicate nominal characteristics.

* S-PARAMETERS (TA = +25°C, Vcc = VAGc = 5.0 V)

S11-FREQUENCY



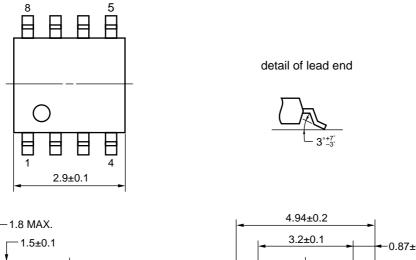
S22-FREQUENCY

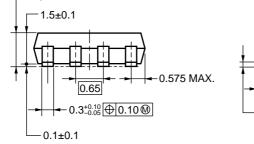


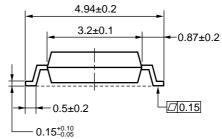
Data Sheet PU10171EJ03V0DS

PACKAGE DIMENSIONS

8-PIN PLASTIC SSOP (4.45 mm (175)) (UNIT: mm)







NOTES ON CORRECT USE

- (1) Observe precautions for handling because of electro-static sensitive devices.
- (2) Form a ground pattern as widely as possible to minimize ground impedance (to prevent undesired oscillation). All the ground pins must be connected together with wide ground pattern to decrease impedance difference.
- (3) The bypass capacitor should be attached to Vcc line.

RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions		Condition Symbol
Infrared Reflow	Peak temperature (package surface temperature) Time at peak temperature Time at temperature of 220°C or higher Preheating time at 120 to 180°C Maximum number of reflow processes Maximum chlorine content of rosin flux (% mass)	: 260°C or below : 10 seconds or less : 60 seconds or less : 120±30 seconds : 3 times : 0.2%(Wt.) or below	IR260
VPS	Peak temperature (package surface temperature) Time at temperature of 200°C or higher Preheating time at 120 to 150°C Maximum number of reflow processes Maximum chlorine content of rosin flux (% mass)	: 215°C or below : 25 to 40 seconds : 30 to 60 seconds : 3 times : 0.2%(Wt.) or below	VP215
Wave Soldering	Peak temperature (molten solder temperature) Time at peak temperature Preheating temperature (package surface temperature) Maximum number of flow processes Maximum chlorine content of rosin flux (% mass)	: 260°C or below : 10 seconds or less : 120°C or below : 1 time : 0.2%(Wt.) or below	WS260
Partial Heating	Peak temperature (pin temperature) Soldering time (per side of device) Maximum chlorine content of rosin flux (% mass)	: 350°C or below : 3 seconds or less : 0.2%(Wt.) or below	H\$350

Caution Do not use different soldering methods together (except for partial heating).

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M8E 00.4-0110

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CEL certifies, to its knowledge, that semiconductor and laser products detailed below are compliant with the requirements of European Union (EU) Directive 2002/95/EC Restriction on Use of Hazardous Substances in electrical and electronic equipment (RoHS) and the requirements of EU Directive 2003/11/EC Restriction on Penta and Octa BDE.

CEL Pb-free products have the same base part number with a suffix added. The suffix –A indicates that the device is Pb-free. The –AZ suffix is used to designate devices containing Pb which are exempted from the requirement of RoHS directive (*). In all cases the devices have Pb-free terminals. All devices with these suffixes meet the requirements of the RoHS directive.

This status is based on CEL's understanding of the EU Directives and knowledge of the materials that go into its products as of the date of disclosure of this information.

Restricted Substance per RoHS	Concentration Limit per RoHS (values are not yet fixed)	Concentratio in CEL		
Lead (Pb)	< 1000 PPM	-A Not Detected	-AZ (*)	
Mercury	< 1000 PPM	Not Detected		
Cadmium	< 100 PPM	Not Detected		
Hexavalent Chromium	< 1000 PPM	Not Detected		
РВВ	< 1000 PPM	Not Detected		
PBDE	< 1000 PPM	Not Detected		

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